

7-segment LED chip

ELC-660-199

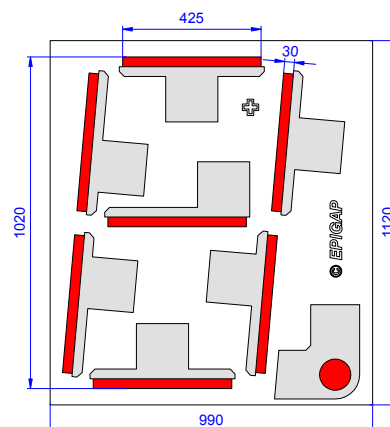
Color	Type	Technology	Electrodes
Red	ELC-660-199	GaAsP/GaAs diffusion type	P (anode) up

Outline (dimensions in microns)

Application: This miniature device is an excellent choice for applications where small size and reduced space are important factors such as complex displays in optical devices for laboratory, measurement, control- and medical equipment.

Contact metallization: anode- aluminum, cathode- Au alloy.

Chip thickness- 290 μm .



Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions*	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.7	2.0	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Luminous intensity/segment	$I_F = 20 \text{ mA}$	I_V	180	300		μcd
Luminous intensity ratio segment to segment	$I_F = 20 \text{ mA}$				1.75	
Luminous intensity ratio to adjacent chip	$I_F = 20 \text{ mA}$				2.00	
Peak wavelength	$I_F = 20 \text{ mA}$	λ_p	650	660	670	nm
Spectral bandwidth at 50%	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		17		nm

* Current for one segment

Labeling

Type	Lot N°	I_V (typ, min, max)	Quantity
ELC-660-199			

Packing

Chips in wafer pack or on adhesive film with wire-bond side on top